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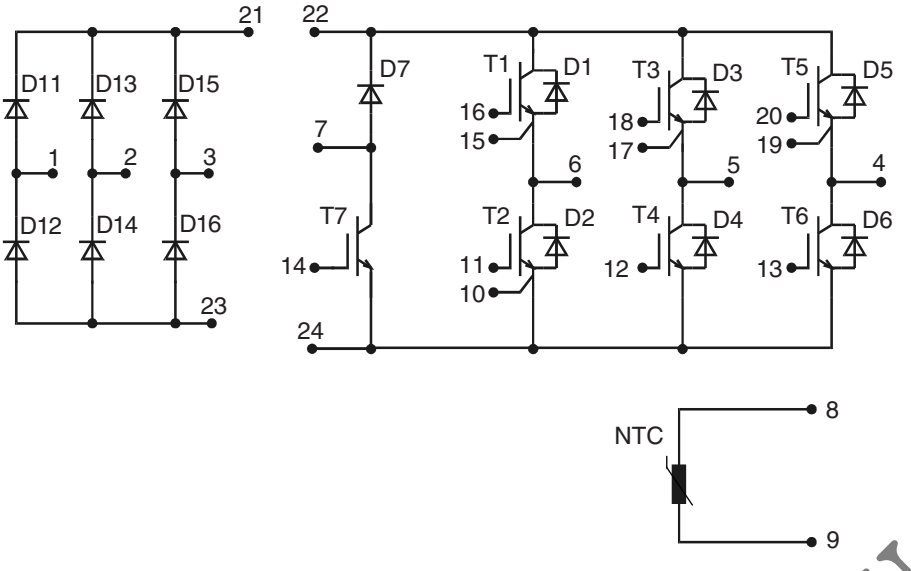
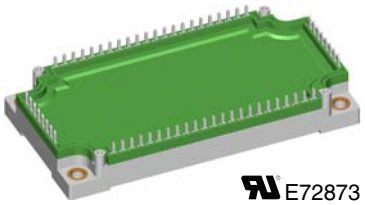
Converter - Brake - Inverter Module (CBI3)





See outline drawing for pin arrangement

Three Phase Rectifier	Brake Chopper	Three Phase Inverter
V_{RRM} = 1600 V	V_{CES} = 1200 V	V_{CES} = 1200 V
I_{FAVM} = 70 A	I_{C25} = 52 A	I_{C25} = 90 A
I_{FSM} = 700 A	$V_{CE(sat)}$ = 2.2 V	$V_{CE(sat)}$ = 1.9 V

Input Rectifier Bridge D11 - D16

Symbol	Conditions	Maximum Ratings	
V_{RRM}		1600	V
I_{FAV}	T_C = 80°C; sine 180°	50	A
I_{DAVM}	T_C = 80°C; rectangular; d = ⅓; bridge	140	A
I_{FSM}	T_{VJ} = 25°C; t = 10 ms; sine 50 Hz	700	A
P_{tot}	T_C = 25°C	135	W

Symbol	Conditions	Characteristic Values (T_{VJ} = 25°C, unless otherwise specified) min.	typ.	max.	
V_F	I_F = 50 A; T_{VJ} = 25°C		1.1	1.3	V
	T_{VJ} = 125°C		1.1		V
I_R	$V_R = V_{RRM}$; T_{VJ} = 25°C			0.05	mA
	T_{VJ} = 125°C		0.8		mA
R_{thJC}	(per diode)			0.94	K/W

Application: AC motor drives with

- Input from single or three phase grid
- Three phase synchronous or asynchronous motor
- electric braking operation

Features

- High level of integration - only one power semiconductor module required for the whole drive
- IGBT technology with low saturation voltage, low switching losses and tail current, high RBSOA and short circuit ruggedness
- Epitaxial free wheeling diodes with Hiperfast and soft reverse recovery
- Industry standard package with insulated copper base plate and soldering pins for PCB mounting
- Temperature sense included

Output Inverter T1 - T6

Symbol	Conditions	Maximum Ratings	
V_{CES}	T_{VJ} = 25°C to 150°C	1200	V
V_{GES}	Continuous	± 20	V
I_{C25}	T_C = 25°C	90	A
I_{C80}	T_C = 80°C	62	A
I_{CM}	V_{GE} = ±15 V; R_G = 22 Ω; T_{VJ} = 125°C	100	A
V_{CEK}	RBSOA; Clamped inductive load; L = 100 µH	V_{CES}	
t_{SC} (SCSOA)	V_{CE} = 900 V; V_{GE} = ±15 V; R_G = 22 Ω; T_{VJ} = 125°C non-repetitive	10	µs
P_{tot}	T_C = 25°C	350	W

Symbol	Conditions	Characteristic Values (T_{VJ} = 25°C, unless otherwise specified) min.	typ.	max.	
$V_{CE(sat)}$	I_C = 50 A; V_{GE} = 15 V; T_{VJ} = 25°C		1.9	2.4	V
	T_{VJ} = 125°C		2.1		V
$V_{GE(th)}$	I_C = 2 mA; V_{GE} = V_{CE}	4.5		6.5	V
I_{CES}	V_{CE} = V_{CES}; V_{GE} = 0 V; T_{VJ} = 25°C			0.8	mA
	T_{VJ} = 125°C		0.8		mA
I_{GES}	V_{CE} = 0 V; V_{GE} = ± 20 V			200	nA
$t_{d(on)}$	Inductive load, T_{VJ} = 125°C		80		ns
t_r	V_{CE} = 600 V; I_C = 50 A		50		ns
$t_{d(off)}$	V_{GE} = ±15 V; R_G = 22 Ω		680		ns
t_f			30		ns
E_{on}			6		mJ
E_{off}			4		mJ
C_{ies}	V_{CE} = 25 V; V_{GE} = 0 V; f = 1 MHz		3.8		nF
Q_{Gon}	V_{CE} = 600 V; V_{GE} = 15 V; I_C = 50 A		350		nC
R_{thJC}	(per IGBT)			0.35	K/W

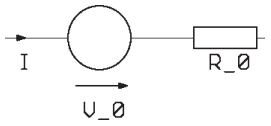
Output Inverter D1 - D6

Symbol	Conditions	Maximum Ratings	
I_{F25}	T_C = 25°C	110	A
I_{F80}	T_C = 80°C	70	A

Symbol	Conditions	Characteristic Values min.	typ.	max.	
V_F	I_F = 50 A; V_{GE} = 0 V; T_{VJ} = 25°C		2.1	2.5	V
	T_{VJ} = 125°C		1.5		V
I_{RM}	I_F = 60 A; di_F/dt = -500 A/µs; T_{VJ} = 125°C		41		A
t_{rr}	V_R = 600 V; V_{GE} = 0 V		200		ns
R_{thJC}	(per diode)			0.61	K/W

Equivalent Circuits for Simulation

Conduction



IGBT (typ. at V_{GE} = 15 V; T_J = 125°C)
T1-T6
V_0 = 0.98 V; R_0 = 23.2 mΩ
T7
V_0 = 0.95 V; R_0 = 45 mΩ

Diode (typ. at T_J = 125°C)
D1-D6
V_0 = 1.27 V; R_0 = 5.8 mΩ
D7
V_0 = 1.25 V; R_0 = 31.2 mΩ
D11-D16
V_0 = 0.83 V; R_0 = 5.5 mΩ

Brake Chopper T7

Symbol	Conditions	Maximum Ratings	
V_{CES}	T_{VJ} = 25°C to 150°C	1200	V
V_{GES}	Continuous	± 20	V
I_{C25}	T_C = 25°C	52	A
I_{C80}	T_C = 80°C	35	A
I_{CM}	V_{GE} = ±15 V; R_G = 39 Ω; T_{VJ} = 125°C	50	A
V_{CEK}	RBSOA; Clamped inductive load; L = 100 µH	V_{CES}	
t_{SC} (SCSOA)	V_{CE} = 900 V; V_{GE} = ±15 V; R_G = 39 Ω; T_{VJ} = 125°C non-repetitive	10	µs
P_{tot}	T_C = 25°C	225	W

Symbol	Conditions	Characteristic Values (T_{VJ} = 25°C, unless otherwise specified) min.	typ.	max.	
$V_{CE(sat)}$	I_C = 35 A; V_{GE} = 15 V; T_{VJ} = 25°C		2.2	2.8	V
	T_{VJ} = 125°C		2.5		V
$V_{GE(th)}$	I_C = 1 mA; V_{GE} = V_{CE}	4.5		6.5	V
I_{CES}	V_{CE} = V_{CES}; V_{GE} = 0 V; T_{VJ} = 25°C			0.1	mA
	T_{VJ} = 125°C		0.1		mA
I_{GES}	V_{CE} = 0 V; V_{GE} = ± 20 V			200	nA
$t_{d(on)}$	Inductive load, T_{VJ} = 125°C		85		ns
t_r	V_{CE} = 600 V; I_C = 35 A		50		ns
$t_{d(off)}$	V_{GE} = ±15 V; R_G = 39 Ω		440		ns
t_f			50		ns
E_{off}			2.6		mJ
C_{ies}	V_{CE} = 25 V; V_{GE} = 0 V; f = 1 MHz		2		nF
Q_{Gon}	V_{CE} = 600 V; V_{GE} = 15 V; I_C = 35 A		150		nC
R_{thJC}				0.55	K/W

Brake Chopper D7

Symbol	Conditions	Maximum Ratings	
V_{RRM}	T_{VJ} = 25°C to 150°C	1200	V
I_{F25}	T_C = 25°C	25	A
I_{F80}	T_C = 80°C	16	A

Symbol	Conditions	Characteristic Values min.	typ.	max.	
V_F	I_F = 35 A; T_{VJ} = 25°C		3.0	3.4	V
	T_{VJ} = 125°C		2.3		V
I_R	V_R = V_{RRM}; T_{VJ} = 25°C			0.1	mA
	T_{VJ} = 125°C		0.1		mA
I_{RM}	I_F = 15 A; di_F/dt = -400 A/µs; T_{VJ} = 125°C		16		A
t_{rr}	V_R = 600 V		130		ns
R_{thJC}				2.1	K/W

Temperature Sensor NTC

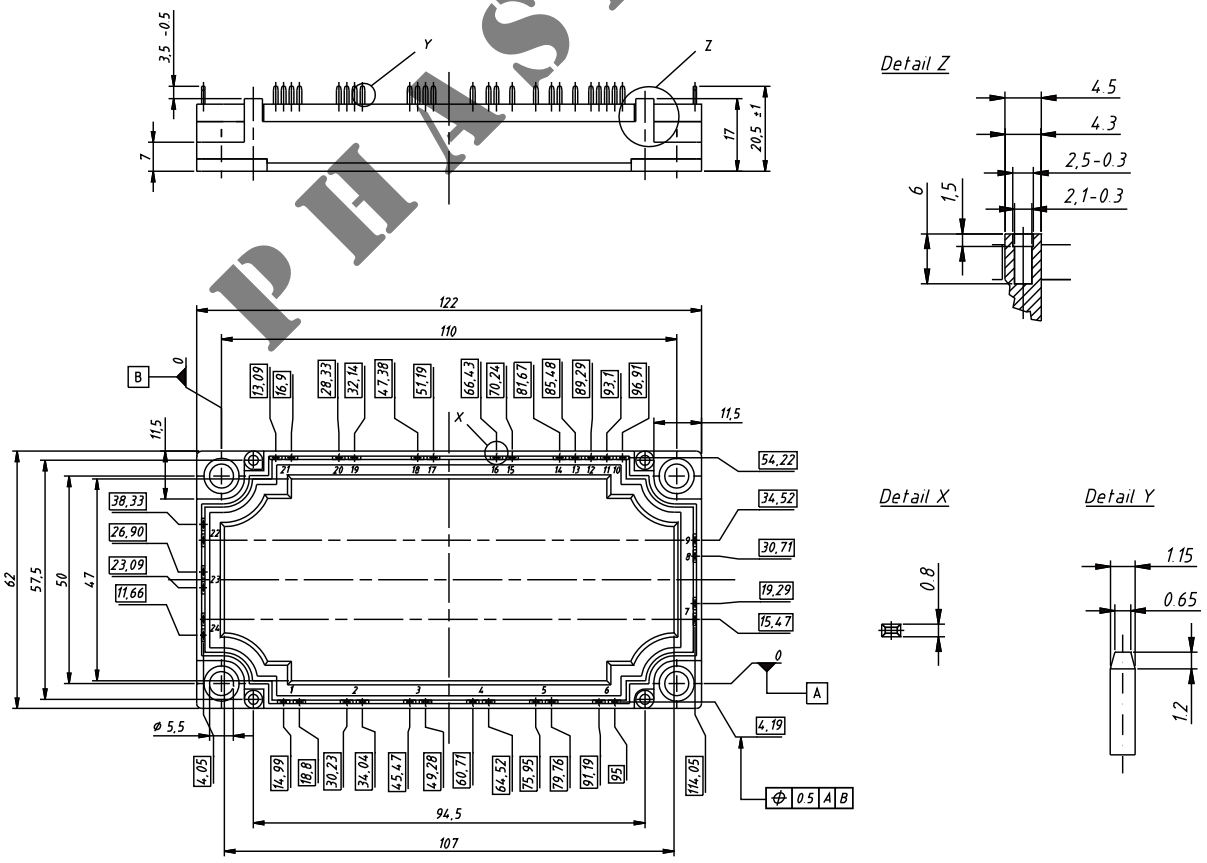
Symbol	Conditions	Characteristic Values min.	typ.	max.	
R_{25}	T = 25°C	4.75	5.0	5.25	kΩ
$B_{25/50}$			3375		K

Module

Symbol	Conditions	Maximum Ratings	
T_{VJ}	operating	-40...+125	°C
T_{JM}		150	°C
T_{stg}		-40...+125	°C
V_{ISOL}	$I_{ISOL} \leq 1$ mA; 50/60 Hz	2500	V~
M_d	Mounting torque (M5)	3 - 6	Nm

Symbol	Conditions	Characteristic Values min.	typ.	max.	
$R_{pin-chip}$			5		mΩ
d_S	Creepage distance on surface	6			mm
d_A	Strike distance in air	6			mm
R_{thCH}	with heatsink compound		0.01		K/W
Weight			300		g

Dimensions in mm (1 mm = 0.0394")



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Input Rectifier Bridge D11 - D16

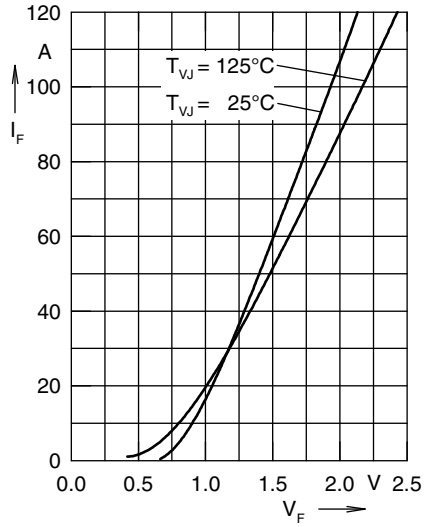

Fig. 1 Forward current versus voltage drop per diode

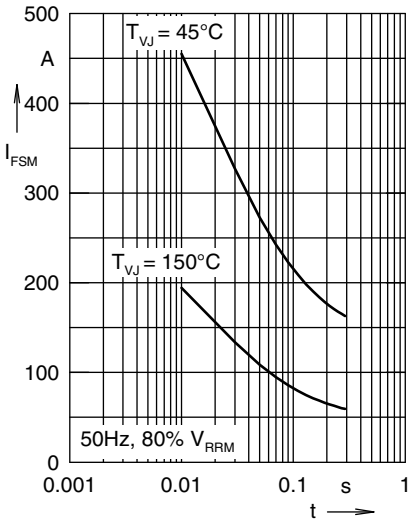

Fig. 2 Surge overload current

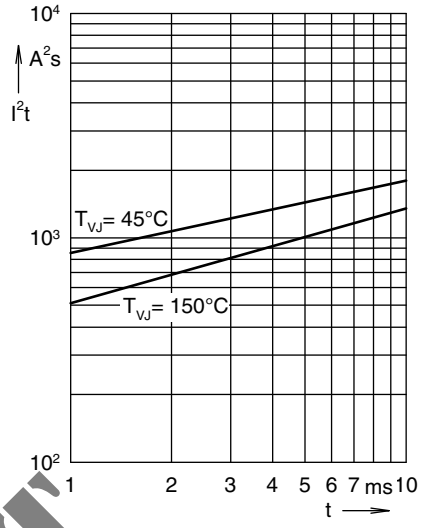

Fig. 3 I^2t versus time per diode

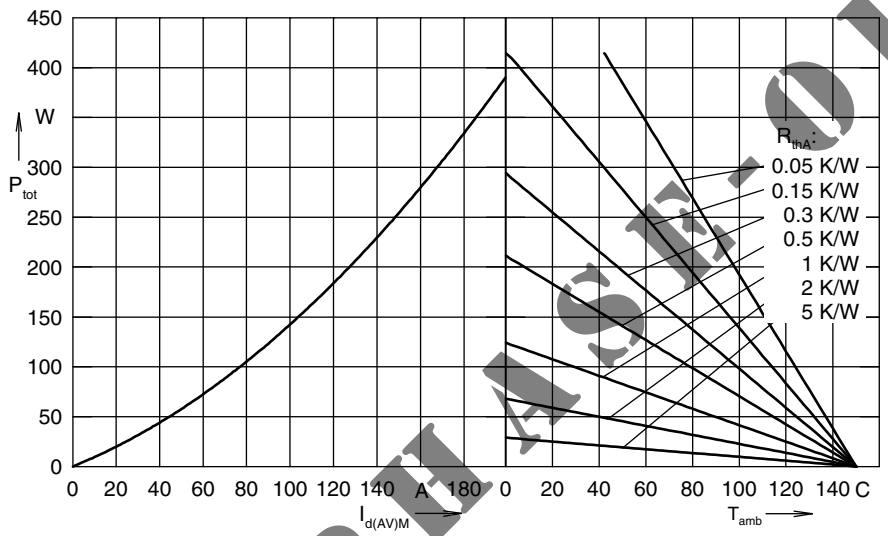

Fig. 4 Power dissipation versus direct output current and ambient temperature, sin 180°

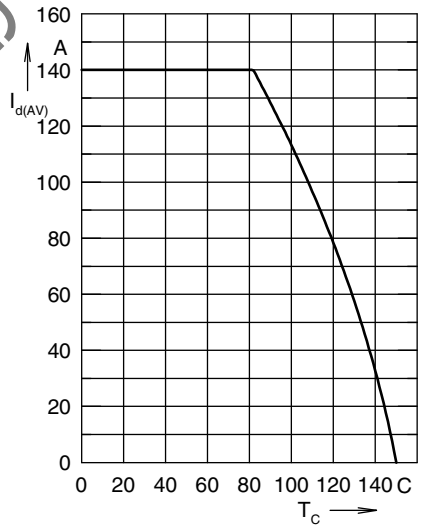

Fig. 5 Max. forward current versus case temperature

Output Inverter T1 - T6 / D1 - D6

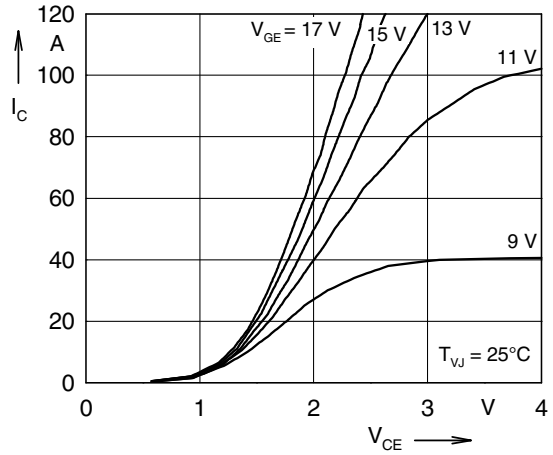

Fig. 7 Typ. output characteristics

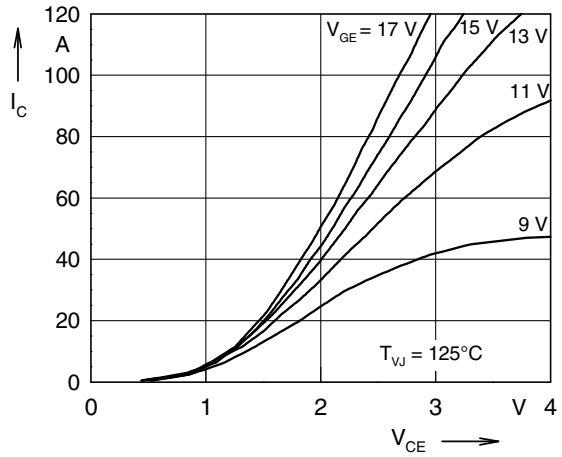

Fig. 8 Typ. output characteristics

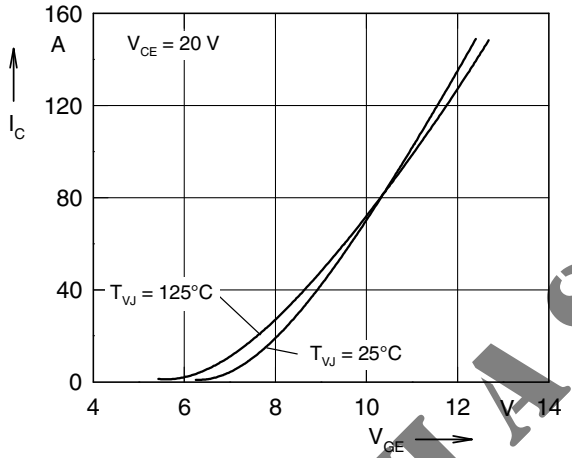

Fig. 9 Typ. transfer characteristics

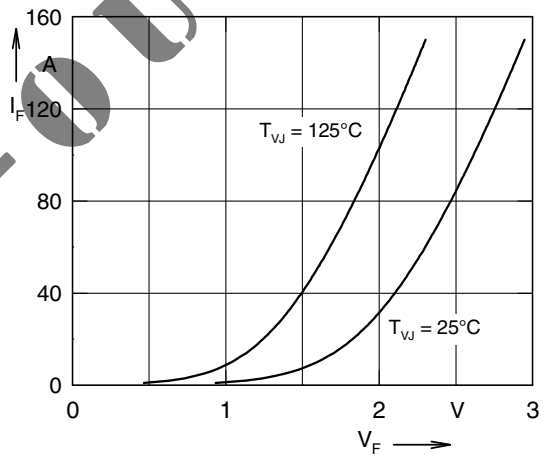

Fig. 10 Typ. forward characteristics of free wheeling diode

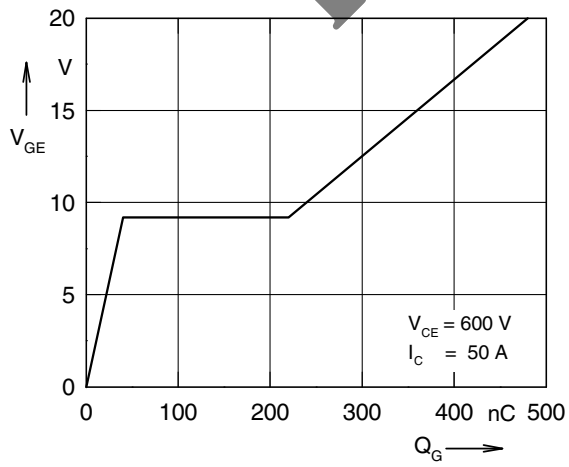

Fig. 11 Typ. turn on gate charge

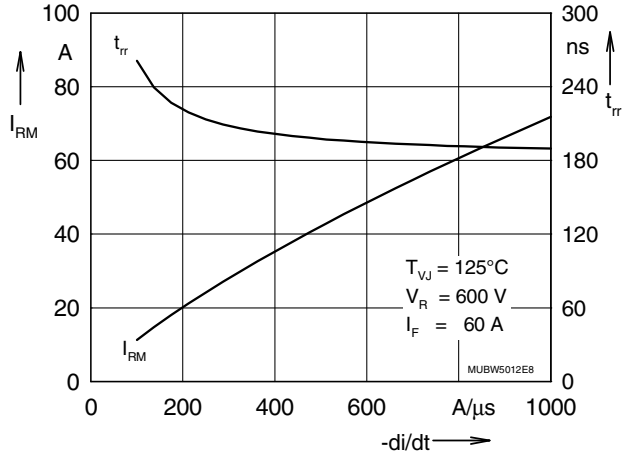

Fig. 12 Typ. turn off characteristics of free wheeling diode

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Output Inverter T1 - T6 / D1 - D6

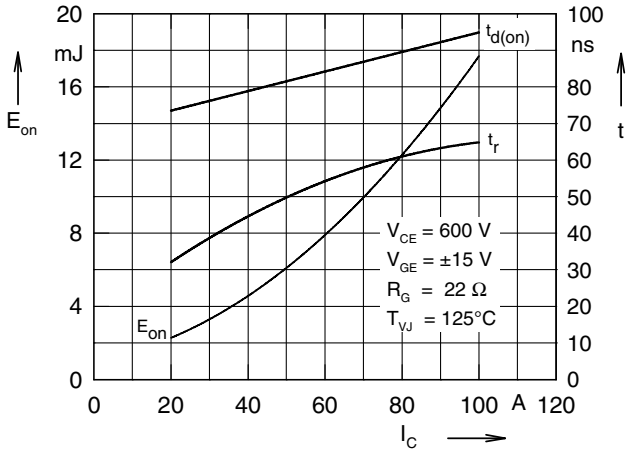

Fig. 13 Typ. turn on energy and switching times versus collector current

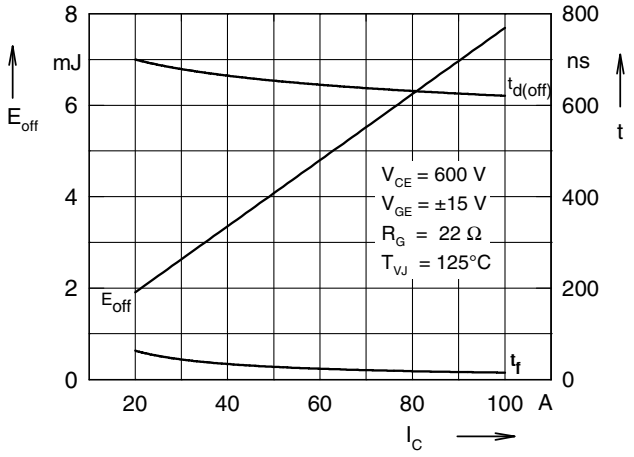

Fig. 14 Typ. turn off energy and switching times versus collector current

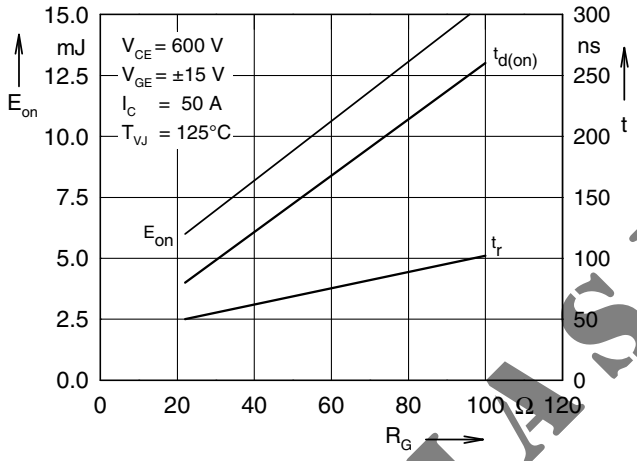

Fig. 15 Typ. turn on energy and switching times versus gate resistor

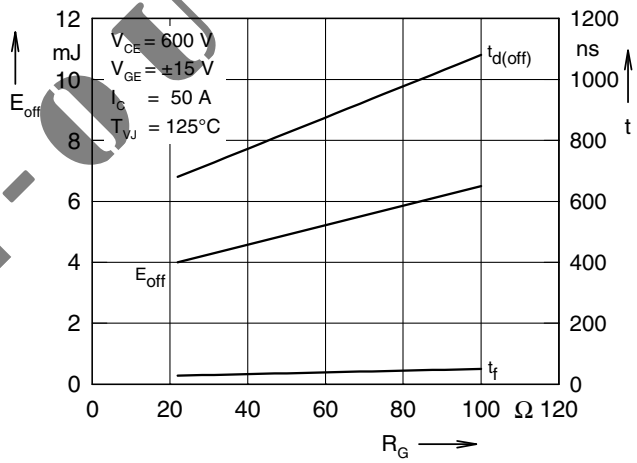

Fig.16 Typ. turn off energy and switching times versus gate resistor

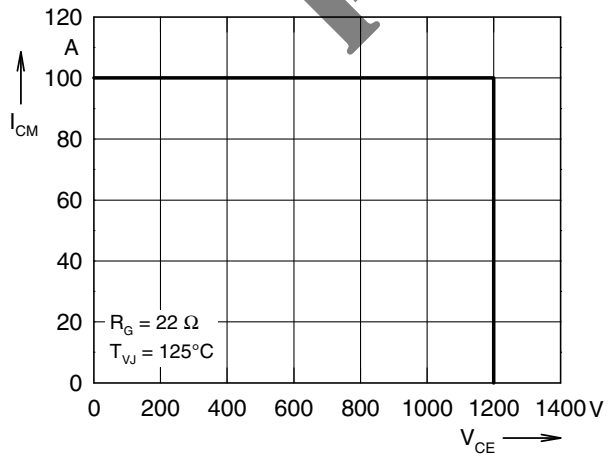

Fig. 17 Reverse biased safe operating area RBSOA

Brake Chopper T7 / D7

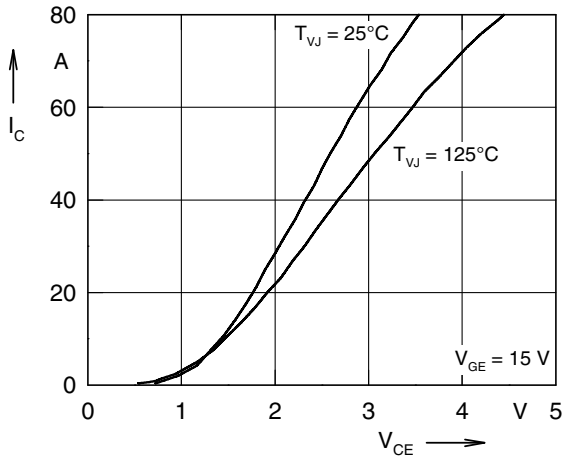

Fig. 19 Typ. output characteristics

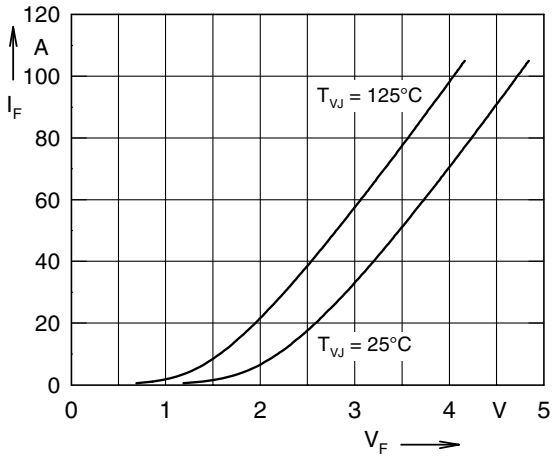

Fig. 20 Typ. forward characteristics of free wheeling diode

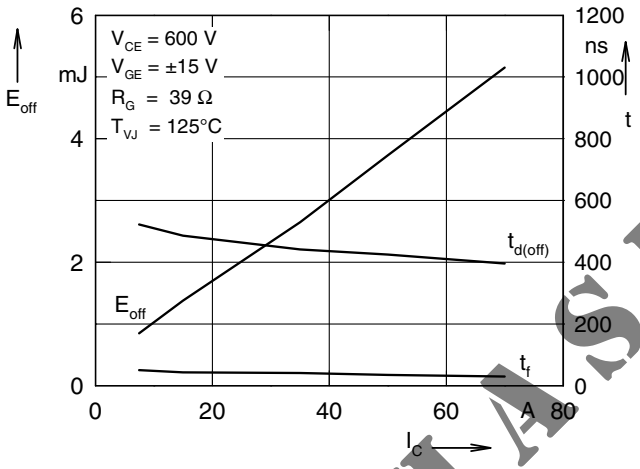

Fig. 21 Typ. turn off energy and switching times versus collector current

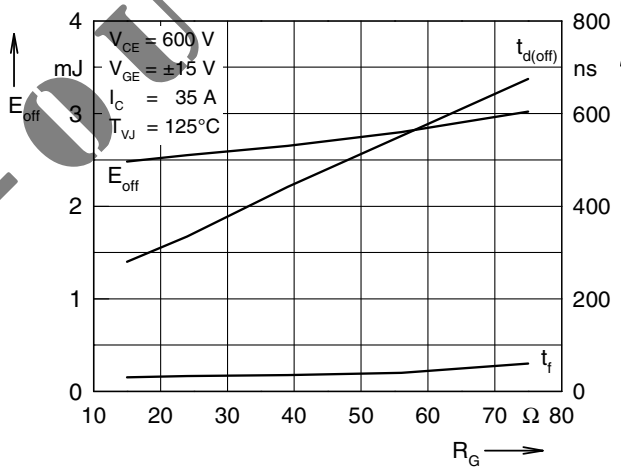

Fig. 22 Typ. turn off energy and switching times versus gate resistor

Temperature Sensor NTC

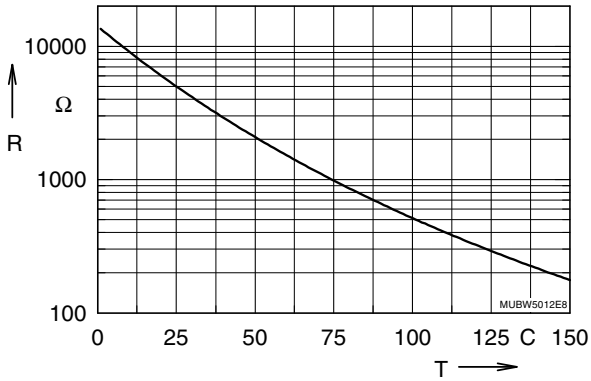

Fig. 24 Typ. thermistorresistance versus temperature

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